

AMENDMENTS TO THE CLAIMS

In the claims:

1. (previously presented) A method of forming a substrate made of a Group III-V nitride compound including at least one element from Group IIIB elements and at least nitrogen (N) from Group VB elements, wherein the substrate is grown on a growth base with a thickness of smaller than or equal to 100 μm , the substrate having a thickness of larger than or equal to 200 μm and a curvature smaller than or equal to 0.03 cm^{-1} , the curvature being caused by a difference in thermal expansion coefficients of the growth base and the substrate.

2. (original) A method of forming a substrate according to claim 1, wherein the growth base made of one selected from a group consisting of sapphire, silicon carbide, spinel, gallium arsenide and silicon is used.

3. (original) A method of forming a substrate according to claim 1, wherein the substrate made of gallium nitride (GaN) is grown.

4. (original) A method of forming a substrate according to claim 1, wherein the substrate is grown by means of hydride vapor phase deposition, halide vapor phase deposition or metal organic chemical vapor deposition.

5. (previously presented) A method of forming a substrate according to claim 1, wherein the substrate is doped with impurities.

6. (original) A method of forming a substrate according to claim 5, wherein at least one selected from a group consisting of carbon (C), silicon (Si), germanium (Ge), tin (Sn), sulfur (S), selenium (Se) and tellurium (Te), or at least one selected from a group consisting of carbon, silicon, germanium, tin, beryllium (Be), magnesium (Mg), calcium (Ca), zinc (Zn) and cadmium (Cd) is doped as the impurities.

7. (original) A method of forming a substrate according to claim 1, further comprising a step of removing the growth base.

8. (original) A method of forming a substrate according to claim 7, wherein the growth base is removed by means of etching, lapping or heat application.

9. (original) A method of forming a substrate according to claim 7, further comprising a step of forming a protecting film to cover the substrate prior to the step of removing the growth base.

10. (original) A method of forming a substrate according to claim 1, further comprising a step of flattening a surface of the substrate.

Please add the following new claims.

11. (new) A method of forming a substrate comprising the steps of:

providing a growth base of a thickness smaller than or equal to 100 μm , said growth base being sapphire, silicon carbide, spinel, gallium arsenide or silicon; and

growing the substrate on said growth base to a thickness greater than or equal to 200 μm , said substrate being a Group III-V nitride compound,

wherein said step of growing the substrate is performed after said step of providing said growth base.

12. (new) A method of forming a substrate according to claim 11, further comprising covering said substrate with a protecting film.

13. (new) A method of forming a substrate according to claim 12, wherein said protecting film is silicon dioxide (SiO_2).

14. (new) A method of forming a substrate according to claim 12, wherein said protecting film is silicon nitride (Si_xN_y).

15. (new) A method of forming a substrate according to claim 12, further comprising a step of removing said growth base from said substrate.

16. (new) A method of forming a substrate according to claim 15, wherein said step of covering said substrate with said protecting film is performed prior to said step of removing said growth base.

17. (new) A method of forming a substrate according to claim 15, further comprising a step of removing said protecting film from said substrate.

18. (new) A method of forming a substrate according to claim 17, wherein said step of removing said protecting film is performed after said step of removing said growth base.

19. (new) A method of forming a substrate according to claim 11, further comprising a step of removing said growth base from said substrate.

20. (new) A method of forming a substrate according to claim 11, wherein said substrate is grown on and in contact with said growth base.

21. (new) A method of forming a substrate according to claim 11, wherein said substrate is grown by means of hydride vapor phase deposition, halide vapor phase deposition, metal organic chemical vapor deposition, or vapor phase epitaxy deposition.

22. (new) A method of forming a substrate according to claim 11, wherein said substrate has a curvature smaller than or equal to 0.03 cm^{-1} .

23. (new) A method of forming a substrate according to claim 11, wherein said curvature is caused by a difference in thermal expansion coefficients of said growth base and said substrate.

24. (new) A method of forming a substrate according to claim 11, wherein said substrate is doped with impurities.

25. (new) A method of forming a substrate according to claim 24, wherein at least one selected from a group consisting of carbon (C), silicon (Si), germanium (Ge), tin (Sn), sulfur (S), selenium (Se) and tellurium (Te), or at least one selected from a group consisting of carbon, silicon, germanium, tin, beryllium (Be), magnesium (Mg), calcium (Ca), zinc (Zn) and cadmium (Cd) is doped as the impurities.